

December 2013

FDPF3860T

N-Channel PowerTrench[®] MOSFET 100 V, 20 A, 38.2 m Ω

Features

- $R_{DS(on)}$ = 29.1 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 5.9 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- · High Power and Current Handling Capability
- · RoHS Compliant

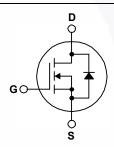
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Consumer Appliances
- LCD/LED/PDP TV
- · Synchronous Rectification
- · Uninterruptible Power Supply
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDPF3860T	Unit
V _{DSS}	Drain to Source Voltage			100	V
V _{GSS}	Gate to Source Voltage			±20	V
	- Continuous (T _C = 25°C)			20	_
ID	Drain Current	- Continuous (T _C = 100°C)		12.7	A
I _{DM}	Drain Current	- Pulsed	(Note 1)	80	Α
E _{AS}	Single Pulsed Avalanche	e Energy	(Note 2)	278	mJ
I _{AR}	Avalanche Current		(Note 1)	20	Α
E _{AR}	Repetitive Avalanche Er	nergy	(Note 1)	3.4	mJ
dv/dt	Peak Diode Recovery dv	v/dt	(Note 3)	15	V/ns
D	Dower Dissipation	$(T_C = 25^{\circ}C)$		33.8	W
P_{D}	Power Dissipation	- Derate Above 25°C		0.27	W/°C
T _J , T _{STG}	Operating and Storage	Temperature Range		-55 to +150	°C
TL	Maximum Lead Tempera	ature for Soldering, 1/8" from Case fo	r 5 Seconds	300	οС

Thermal Characteristics

Symbol	Parameter FDPF386		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		30/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF3860T	FDPF3860T	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	100	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 80 V, V _{GS} = 0 V	-	-	1	μА
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 48 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 5.9 \text{ A}$	-	29.1	38.2	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 5.9 A	-	21	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	-	1350	1800	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	145	190	pF
C _{rss}	Reverse Transfer Capacitance	1 10112	1	60	90	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time			-	15	40	ns
t _r	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_{D} = 5.9 \text{ A},$		-	17	45	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 6 Ω		-	24	60	ns
t _f	Turn-Off Fall Time		(Note 4)	-	7	25	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 80 V, I _D = 5.9 A,		-	23	35	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V		-	7	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	- /	8	-	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	80	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 5.9 A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 5.9 A,	-	40	-	ns
Q_{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	56	-	nC

Notes:

- Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 16 mH, I_{AS} = 5.9 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
- 3. I $_{SD} \leq 5.9$ A, di/dt ≤ 200 A/µs, V $_{DD} \leq BV _{DSS},$ starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

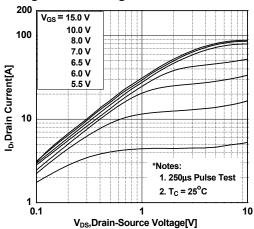


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

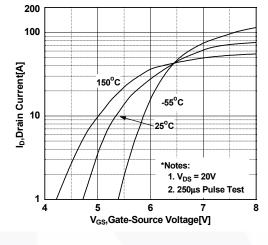


Figure 2. Transfer Characteristics

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

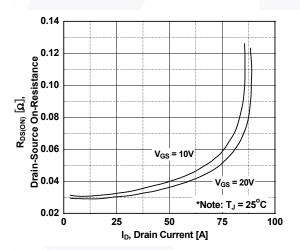
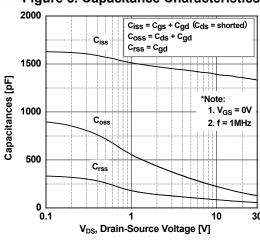


Figure 5. Capacitance Characteristics



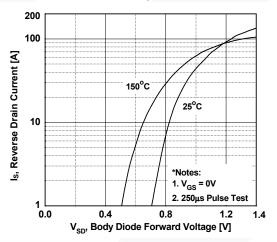
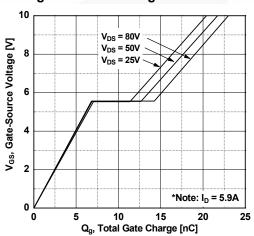


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

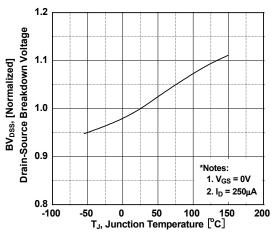


Figure 8. On-Resistance Variation vs. Temperature

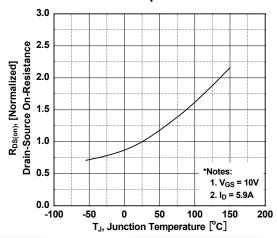


Figure 9. Maximum Safe Operating Area

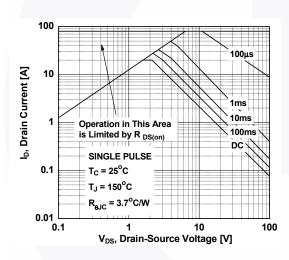


Figure 10. Maximum Drain Current vs. Case Temperature

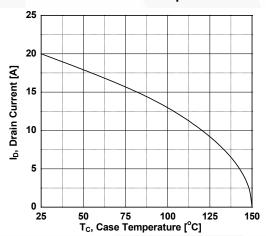
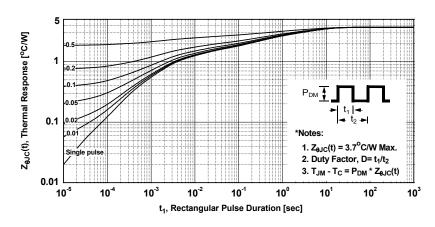


Figure 11. Transient Thermal Response Curve



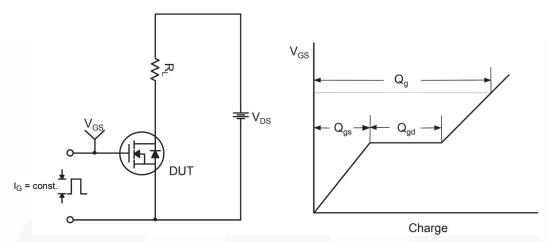


Figure 12. Gate Charge Test Circuit & Waveform

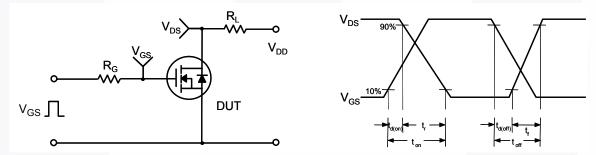


Figure 13. Resistive Switching Test Circuit & Waveforms

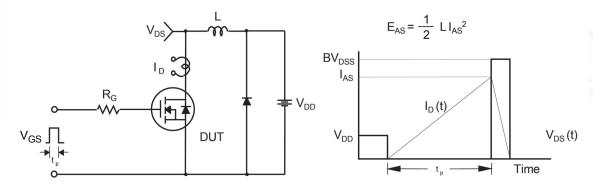


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

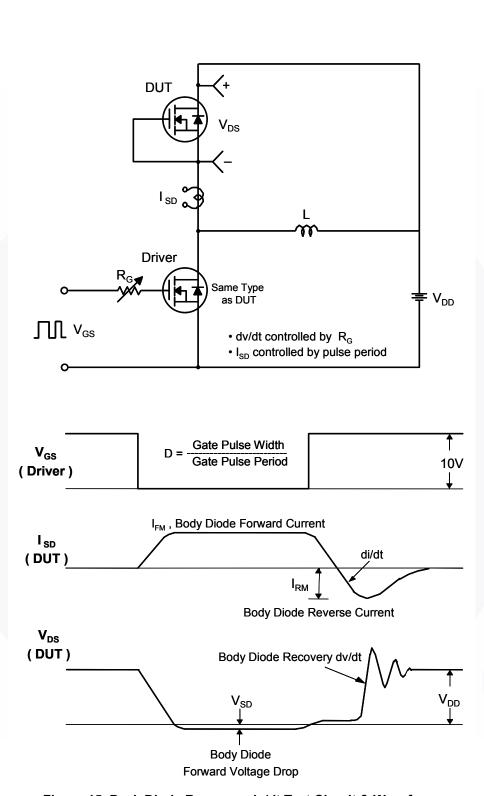


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

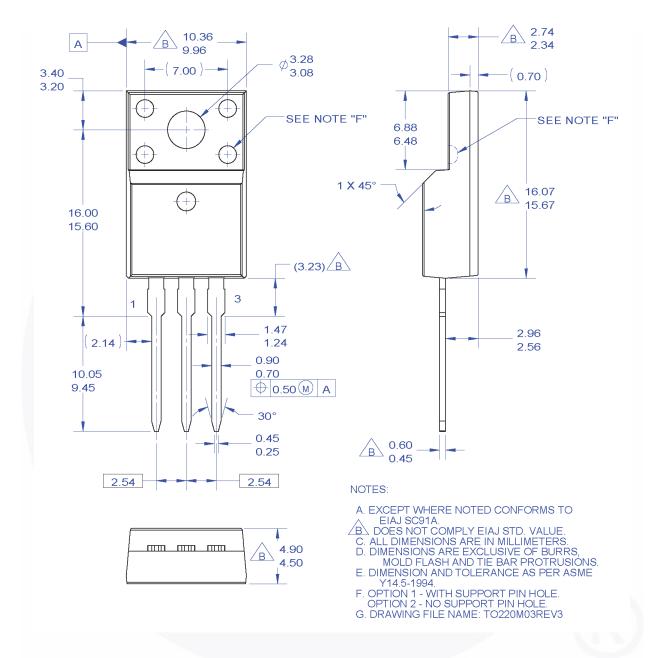


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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